

# RJL5014DPP

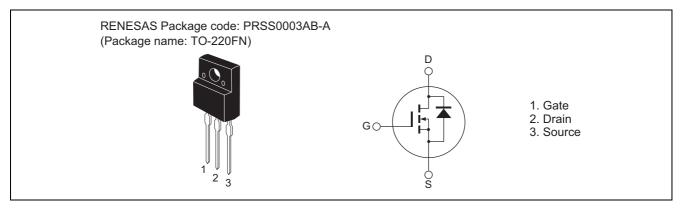
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1690-0300 Rev.3.00 Jun 13, 2008

# Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	500	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub> <sup>Note4</sup>	19	А
Drain peak current	Note1	57	А
Body-drain diode reverse drain current	I <sub>DR</sub>	19	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	57	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	4	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	0.88	mJ
Channel dissipation	Pch Note2	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

- 2. Value at Tc =  $25^{\circ}$ C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

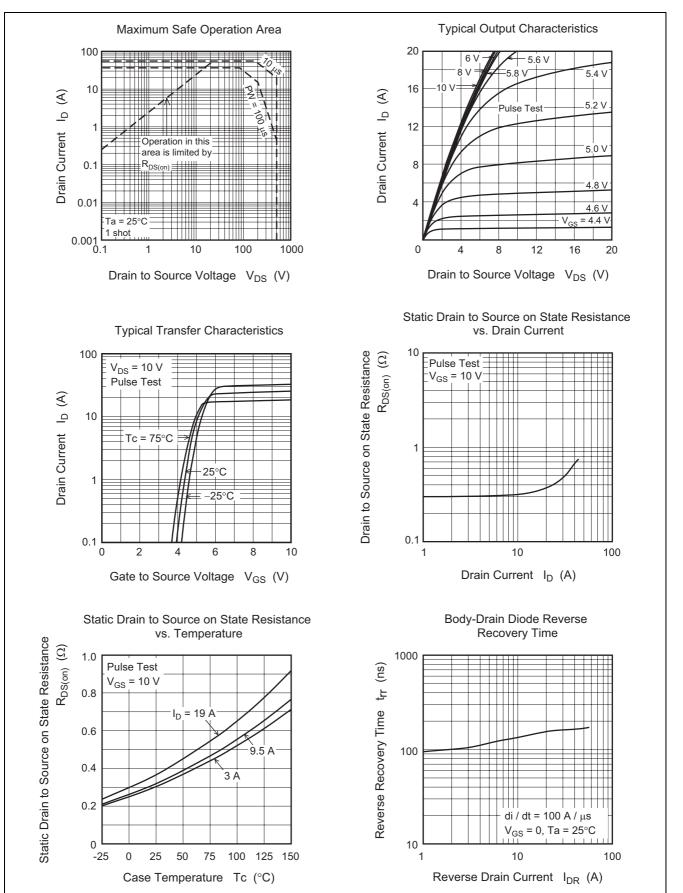
**AFOO** 

# **Electrical Characteristics**

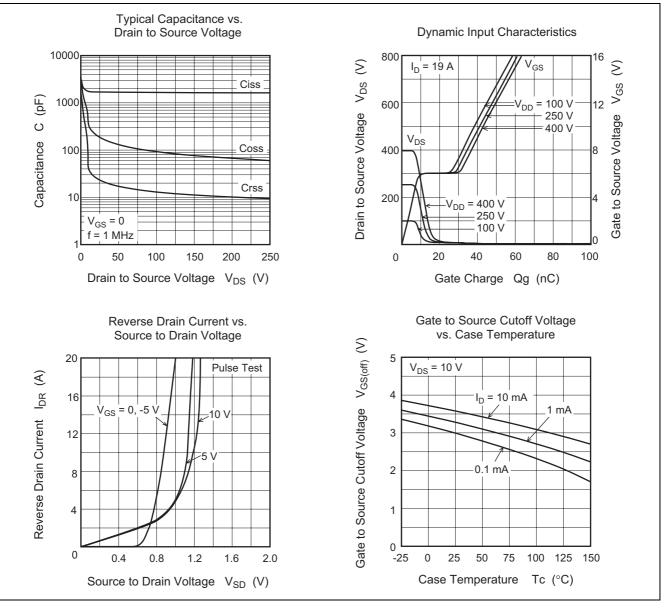
						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	500		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		—	10	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$		0.32	0.40	Ω	$I_D = 9.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
Input capacitance	Ciss	_	1700	—	pF	$V_{DS} = 25 V$ $V_{GS} = 0$ $f = 1 MHz$
Output capacitance	Coss	_	190	—	pF	
Reverse transfer capacitance	Crss		23	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	32	_	ns	$I_{D} = 9.5 \text{ A} \\ V_{GS} = 10 \text{ V} \\ R_{L} = 26.3 \Omega \\ Rg = 10 \Omega$
Rise time	tr	-	27	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	-	95	—	ns	
Fall time	t <sub>f</sub>		20	—	ns	
Total gate charge	Qg		43	—	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	-	8.2	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 19 A
Gate to drain charge	Qgd	_	21.8	_	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	1.00	1.65	V	$I_F = 19 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>		160	_	ns	$I_F = 19 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

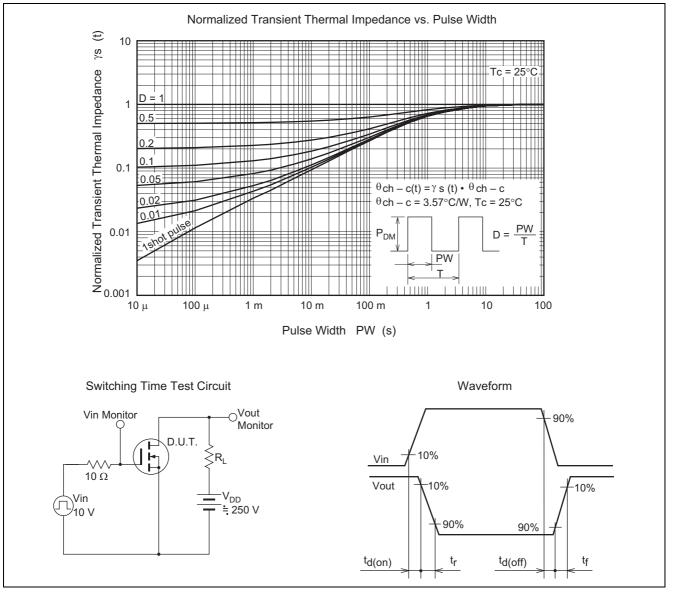
Notes: 5. Pulse test

### **Main Characteristics**

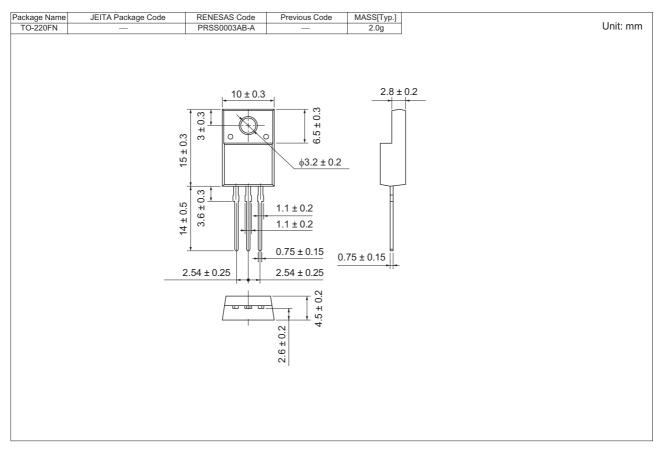


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJL5014DPP-00-T2	1050 pcs	Box (Tube)

http://www.renesas.com

# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

# Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510